

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	2	(("20020045289") or ("20020084252")).PN.	US-PGPUB; USPAT
2	BRS	L2	2	("2002/0045289").URPN.	USPAT
3	BRS	L3	1740	(self adj assembl\$4) with monolayer	USPAT
4	BRS	L5	67	3 with (cu or copper)	USPAT
5	BRS	L6	187	3 with electrode	USPAT
6	BRS	L7	86	3 with silane	USPAT
7	BRS	L4	3	3 with wiring	USPAT
8	BRS	L8	22	3 same (tft or (thin adj film adj transistor))	USPAT
9	BRS	L9	53	3 same (pixel or display)	USPAT
10	BRS	L10	6365	trimethoxysilane	USPAT
11	BRS	L11	139	3 and 10	USPAT

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2941	(self adj assembl\$4) with monolayer	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	76	1 with (cu or copper)	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	1	("2006/0163582").URPN.	USPAT
4	BRS	L4	0	1 with electrode	USPAT
5	BRS	L5	309	1 with electrode	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	197	1 with silane	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	10	1 with wiring	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	54	1 same (tft or (thin adj film adj transistor))	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	124	1 same (pixel or display)	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	7830	trimethoxysilane or (trimethoxy adj silane)	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
11	BRS	L11	172	1 and 10	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	2685	(trimethoxy adj silane)	USPAT
13	BRS	L13	21	12 and ((self adj assembl\$4) with monolayer)	USPAT